What is claimed is:

1. A semiconductor device comprising:

first and second electrodes apart from each other; and

a capacitor dielectric film between the first electrode and the second electrode and including a first dielectric film and a second dielectric film, the first dielectric film and the second dielectric film being stacked,

wherein the first dielectric film includes one of a first monometal oxide film and a first bimetal oxide film,

the first dielectric film has an orthorhombic crystal system,

the second dielectric film includes a paraelectric material,

the second dielectric film has a monoclinic crystal system, and

a dielectric constant of the capacitor dielectric film is greater than a dielectric constant of the second dielectric film.

2. The semiconductor device of claim 1, wherein each of the first dielectric film and the second dielectric film is a single film.

3. The semiconductor device of claim 1, wherein the first dielectric film includes a first sub-dielectric film and a second sub-dielectric film, and

the first sub-dielectric film is between the second sub-dielectric film and the second dielectric film.

4. The semiconductor device of claim 3, wherein the second dielectric film includes a third sub-dielectric film and a fourth sub-dielectric film, and

the third sub-dielectric film is between the fourth sub-dielectric film and the first dielectric film.

5. The semiconductor device of any one of claims 1 to 4, wherein the capacitor dielectric film further includes a third dielectric film including a paraelectric material, and

the first dielectric film is between the second dielectric film and the third dielectric film.

6. The semiconductor device of claim 1, wherein the first dielectric film and the second dielectric film form a dielectric film group, and

the capacitor dielectric film includes a plurality of dielectric film groups.

7. The semiconductor device of any one of claims 1 to 6, wherein the first monometal oxide film includes one of hafnium (Hf) and a rare earth metal of lanthanoids.

8. The semiconductor device of any one of claims 1 to 7, wherein the first bimetal oxide film includes hafnium (Hf) and zirconium (Zr).

9. The semiconductor device of any one of claims 1 to 8, wherein the second dielectric film includes one of a second monometal oxide film and a second bimetal oxide film, and

a metal contained in the second monometal oxide film and the second bimetal oxide film includes at least one of hafnium (Hf) and zirconium (Zr).

10. The semiconductor device of any one of claims 1 to 9, further comprising:

a protection layer between the first electrode and the second electrode and including a metal oxide,

wherein the protection layer is between the first electrode and the capacitor dielectric film and/or between the second electrode and the capacitor dielectric film.

11. The semiconductor device of any one of claims 1 to 10, wherein capacitance of the capacitor dielectric film is greater than capacitance of the second dielectric film.

12. A semiconductor device comprising:

first and second electrodes apart from each other;

a capacitor dielectric film between the first electrode and the second electrode, and including a first dielectric film and a second dielectric film, the first dielectric film including a ferroelectric material, the second dielectric film including a paraelectric material and being between the first dielectric film and the first electrode, the first dielectric film and the second dielectric film being stacked; and

at least one interfacial film including a conductive material and in contact with the first dielectric film,

wherein the first dielectric film has an orthorhombic crystal system and the second dielectric film has a monoclinic crystal system.

13. The semiconductor device of claim 12, wherein the at least one interfacial film is between the second electrode and the first dielectric film.

14. The semiconductor device of claim 12, wherein the at least one interfacial film is between the first dielectric film and the second dielectric film.

15. The semiconductor device of any one of claims 12 to 14, wherein the first dielectric film includes one of a monometal oxide film and a bimetal oxide film.

16. The semiconductor device of claim 15, wherein the monometal oxide film and the bimetal oxide film include the same metal element.

17. A semiconductor device comprising:

a first insulation pattern including a first sidewall and a second sidewall adjacent to each other on a substrate;

a second insulation pattern separate from the first insulation pattern on the substrate and including a third sidewall and a fourth sidewall adjacent to each other, the fourth sidewall of the second insulation pattern facing the second sidewall of the first insulation pattern;

a first lower electrode extending along the first sidewall of the first insulation pattern and not extending along the second sidewall of the first insulation pattern;

a second lower electrode extending along the third sidewall of the second insulation pattern and not extending along the fourth sidewall of the second insulation pattern;

a capacitor dielectric film extending along the first lower electrode, the second lower electrode, the second sidewall of the first insulation pattern and the fourth sidewall of the second insulation pattern, and including a first dielectric film and a second dielectric film, the first dielectric film and the second dielectric film being stacked; and

an upper electrode on the capacitor dielectric film,

wherein the first dielectric film includes one of a monometal oxide film and a bimetal oxide film,

the first dielectric film has an orthorhombic crystal system,

the second dielectric film includes a paraelectric material,

the second dielectric film has a monoclinic crystal system, and

a dielectric constant of the capacitor dielectric film is greater than a dielectric constant of the second dielectric film.

18. The semiconductor device of claim 17, wherein each of the first lower electrode and the second lower electrode includes a portion extending in parallel to an upper surface of the substrate.

19. The semiconductor device of claim 17 or claim 18, wherein each of the first dielectric film and the second dielectric film is a single film.

20. The semiconductor device of any one of claims 17 to 19, wherein the monometal oxide film and the bimetal oxide film include a metal oxide including hafnium.